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<u>Fairchild Semiconductor</u> 2N5962

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Discrete POWER & Signal **Technologies**

2N5962



MMBT5962



NPN General Purpose Amplifier

This device is designed for use as low noise, high gain, general purpose amplifiers requiring collector currents to 50 mA. Sourced from Process 07. See 2N5088 for characteristics.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	45	V
V _{CBO}	Collector-Base Voltage	45	V
V _{EBO}	Emitter-Base Voltage	8.0	V
I _C	Collector Current - Continuous	100	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max Units		Max	
		2N5962	*MMBT5962		
P _D	Total Device Dissipation Derate above 25°C	625 5.0	350 2.8	mW mW/°C	
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3		°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	357	°C/W	

^{*}Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.



NPN General Purpose Amplifier

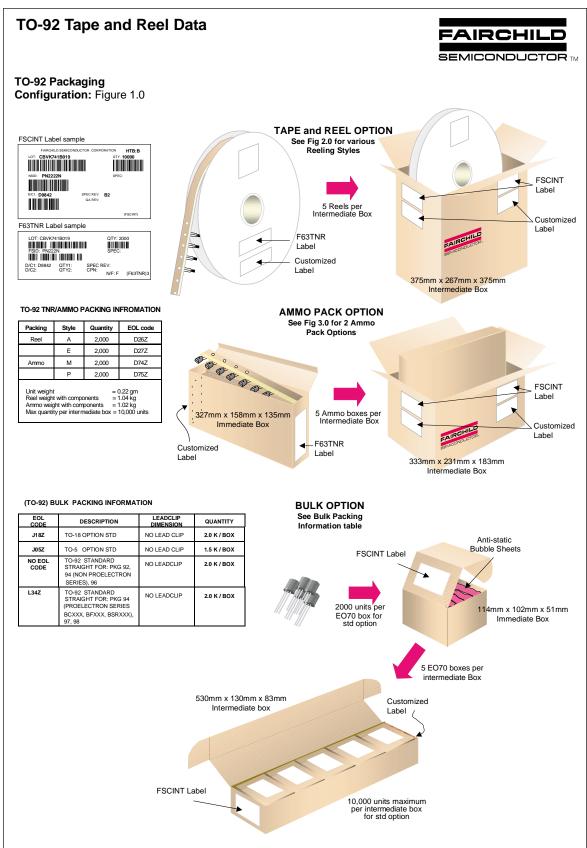
(continued)

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHA	RACTERISTICS				
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage*	$I_C = 5.0 \text{ mA}, I_B = 0$	45		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_{C} = 10 \mu\text{A}, I_{E} = 0$	45		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 10 \mu\text{A}, I_C = 0$	8.0		V
СВО	Collector Cutoff Current	$V_{CB} = 30 \text{ V}, I_{E} = 0$ $V_{CB} = 30 \text{ V}, I_{E} = 0, T_{A} = 65 \text{ °C}$		2.0 50	nA nA
EBO	Emitter Cutoff Current	$V_{EB} = 5.0 \text{ V}, I_{C} = 0$		1.0	nA
		$V_{CE} = 5.0 \text{ V}, I_{C} = 100 \mu\text{A}$ $V_{CE} = 5.0 \text{ V}, I_{C} = 1.0 \text{ mA}$ $V_{CE} = 5.0 \text{ V}, I_{C} = 10 \text{ mA}$	500 550 600	1400	
h _{FE}	DC Current Gain	$V_{CE} = 5.0 \text{ V}, I_{C} = 10 \mu\text{A}$ $V_{CE} = 5.0 \text{ V}, I_{C} = 100 \mu\text{A}$	450 500		
√ _{CE(sat)}	Collector-Emitter Saturation Voltage	$V_{CE} = 5.0 \text{ V}, I_{C} = 10 \text{ mA}$ $I_{C} = 10 \text{ mA}, I_{B} = 0.5 \text{ mA}$	600	1400 0.2	V
/ _{BE(on)}	Base-Emitter On Voltage	$V_{CE} = 5.0 \text{ V}, I_{C} = 1.0 \text{ mA}$	0.5	0.7	V
SMALL S	GIGNAL CHARACTERISTICS Collector-Base Capacitance	V _{CB} = 5.0 V		4.0	pF
Ceb	Emitter-Base Capacitance	V _{EB} = 0.5 V		6.0	pF
lfe	Small-Signal Current Gain	$I_C = 10 \text{ mA}, V_{CE} = 5.0 \text{ V},$ f = 1.0 kHz $I_C = 10 \text{ mA}, V_{CE} = 5.0 \text{ V},$	600	200	
NF	Noise Figure	$\begin{split} &f = 100 \text{ MHz} \\ &V_{CE} = 5.0 \text{ V, } I_{C} = 10 \mu\text{A}, \\ &R_{S} = 10 k\Omega, f = 1.0 \text{ kHz}, \\ &B_{W} = 400 \text{ Hz} \\ &V_{CE} = 5.0 \text{ V, } I_{C} = 100 \mu\text{A}, \end{split}$	1.0	3.0	dB
		$R_S = 1.0 \text{ k}\Omega, f = 1.0 \text{ kHz},$ $B_W = 400 \text{ Hz}$ $V_{CE} = 5.0 \text{ V}, I_C = 100 \mu\text{A},$ $R_C = 10 \text{ k}\Omega, f = 1.0 \text{ kHz}$		6.0	dB
		$R_S = 10 \text{ k}\Omega$, $f = 1.0 \text{ kHz}$, $B_W = 400 \text{ Hz}$ $V_{CE} = 5.0 \text{ V}$, $I_C = 100 \mu\text{A}$,		4.0	dB
		R_S = 100 kΩ, f = 1.0 kHz, B_W = 400 Hz V_{CE} = 5.0 V, I _C = 10 μA, R_S = 10 kΩ, f = 10 Hz -10 kHz		8.0	dB
	1	INS - 10 N22, I = 10 I IZ -10 KMZ		3.0	1

^{*}Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%

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Datasheet of 2N5962 - TRANS NPN 45V 0.1A TO-92



TO-92 Tape and Reel Data, continued

TO-92 Reeling Style Configuration: Figure 2.0





Style "A", D26Z, D70Z (s/h)

Machine Option "E" (J)

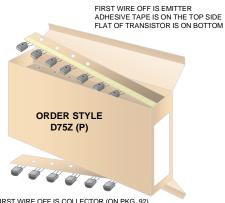


Style "E", D27Z, D71Z (s/h)

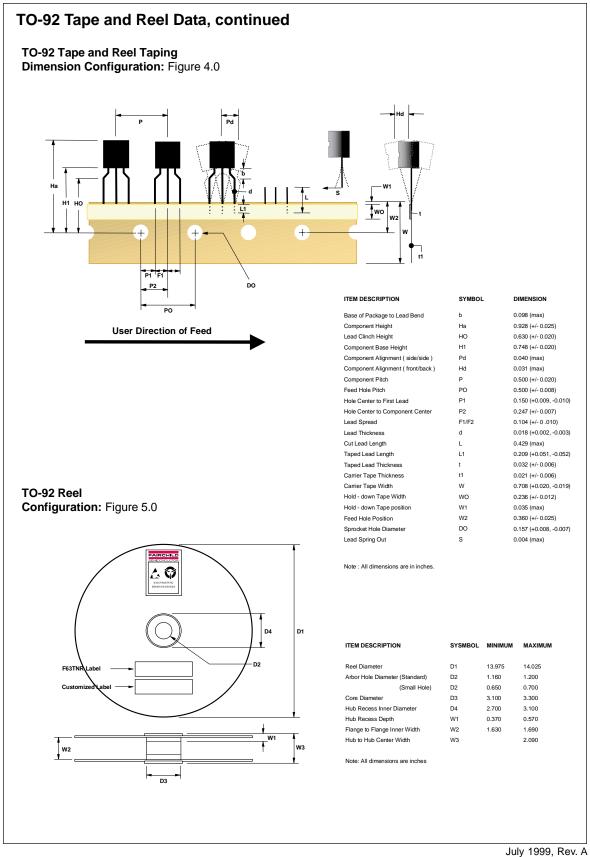
TO-92 Radial Ammo Packaging Configuration: Figure 3.0



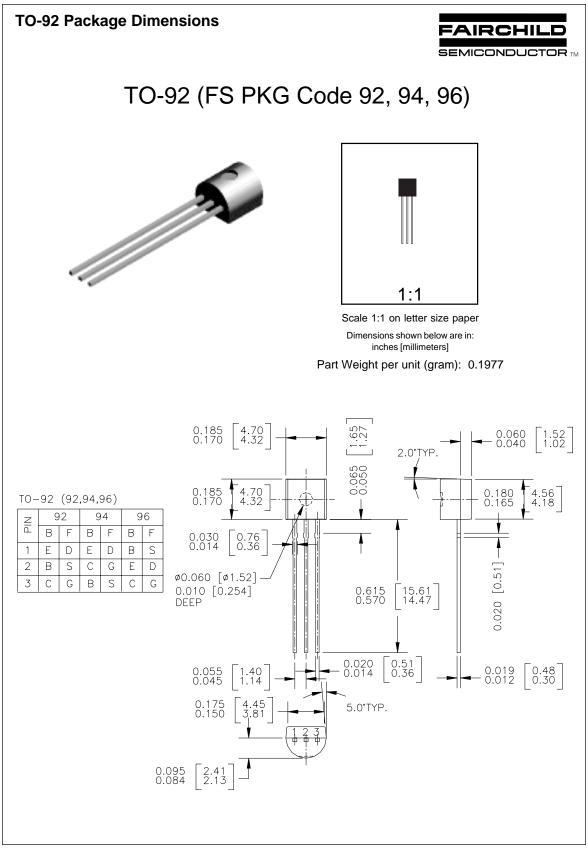
ADHESIVE TAPE IS ON BOTTOM SIDE FLAT OF TRANSISTOR IS ON BOTTOM



FIRST WIRE OFF IS COLLECTOR (ON PKG. 92) ADHESIVE TAPE IS ON BOTTOM SIDE FLAT OF TRANSISTOR IS ON TOP

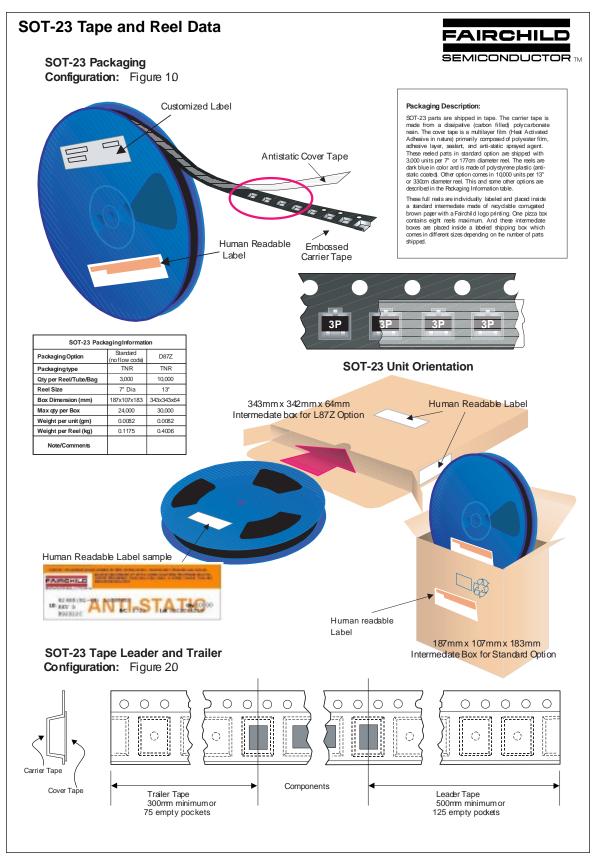




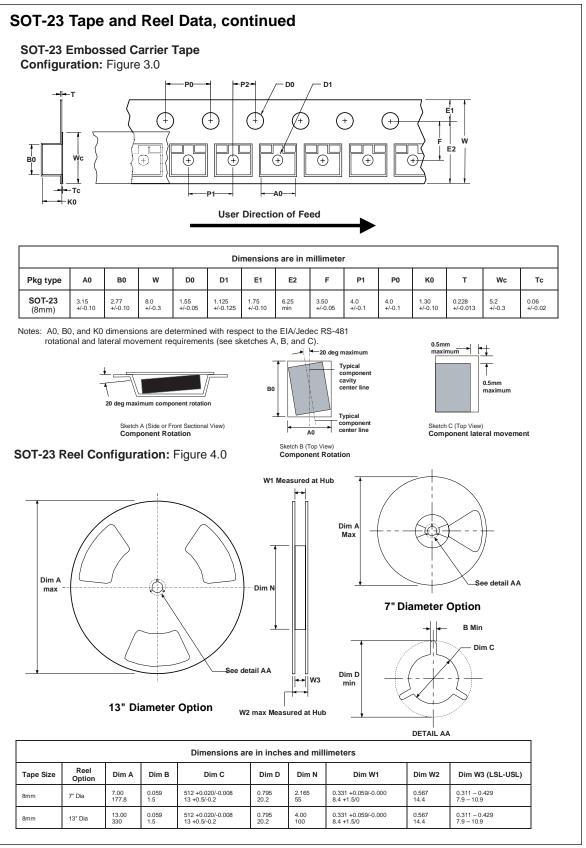


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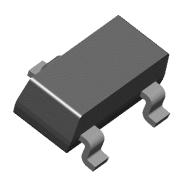


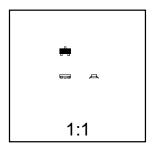


SOT-23 Package Dimensions



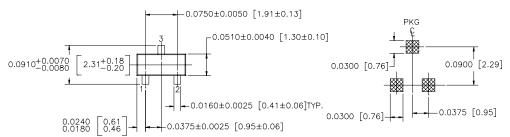
SOT-23 (FS PKG Code 49)



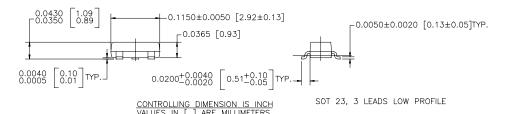


Scale 1:1 on letter size paper Dimensions shown below are in:

inches [millimeters]
Part Weight per unit (gram): 0.0082



LAND PATTERN RECOMMENDATION



NOTE: UNLESS OTHERWISE SPECIFIED

- STANDARD LEAD FINISH 150 MICROINCHES / 3.81 MICROMETERS MINIMUM TIN / LEAD (SOLDER) ON ALLOY 42
- 2. REFERENCE JEDEC REGISTRATION TO-236, VARIATION AB, ISSUE G, DATED JUL 1993



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Datasheet of 2N5962 - TRANS NPN 45V 0.1A TO-92

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